

Dual N-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY

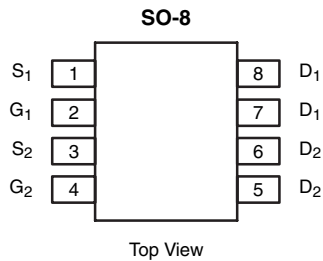
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
20	0.020 at $V_{GS} = 4.5$ V	8.2
	0.030 at $V_{GS} = 2.5$ V	6.7

FEATURES

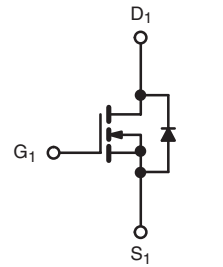
- TrenchFET® Power MOSFETS



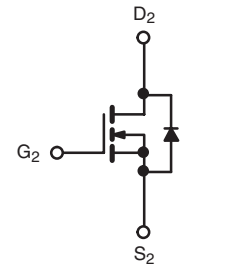
RoHS*
COMPLIANT



Ordering Information: Si9926BDY-T1
Si9926BDY-T1-E3 (Lead (Pb)-free)



N-Channel MOSFET



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ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$, unless otherwise noted

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Parameter		Symbol	10 sec	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current ($T_J = 150\text{ }^{\circ}\text{C}$) ^a	$T_A = 25\text{ }^{\circ}\text{C}$	I_D	8.2	6.2	A
	$T_A = 70\text{ }^{\circ}\text{C}$		6.5	4.9	
Pulsed Drain Current		I_{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I_S	1.7	0.95	
Maximum Power Dissipation ^a	$T_A = 25\text{ }^{\circ}\text{C}$	P_D	2.0	1.14	W
	$T_A = 70\text{ }^{\circ}\text{C}$		1.3	0.72	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	52	62.5	$^\circ\text{C/W}$
		90	110	
Maximum Junction-to-Foot (Drain)	R_{thJF}	32	40	

Notes:

a. Surface Mounted on 1" x 1" FR4 Board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.6		1.5	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 12\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 4.5\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5\text{ V}$, $I_D = 8.2\text{ A}$		0.016	0.020	Ω
		$V_{GS} = 2.5\text{ V}$, $I_D = 3.3\text{ A}$		0.024	0.030	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 8.2\text{ A}$		29		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 1.7\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 8.2\text{ A}$		11	20	nC
Gate-Source Charge	Q_{gs}			2.5		
Gate-Drain Charge	Q_{gd}			3.2		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}$, $R_L = 10\text{ }\Omega$ $I_D \equiv 1\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_G = 6\text{ }\Omega$		35	55	ns
Rise Time	t_r			50	75	
Turn-Off Delay Time	$t_{d(off)}$			31	50	
Fall Time	t_f			15	25	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 1.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		30	60	

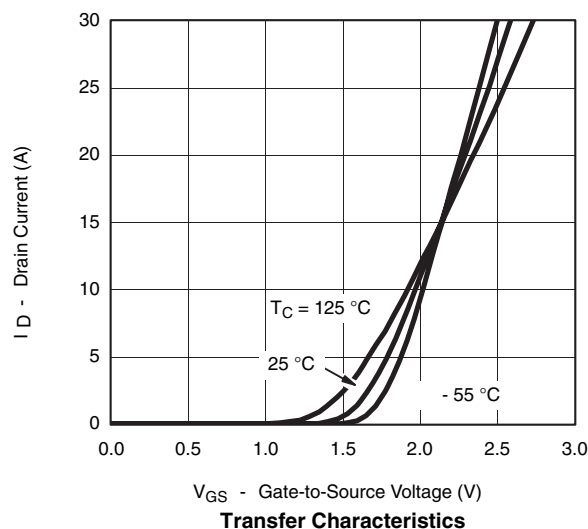
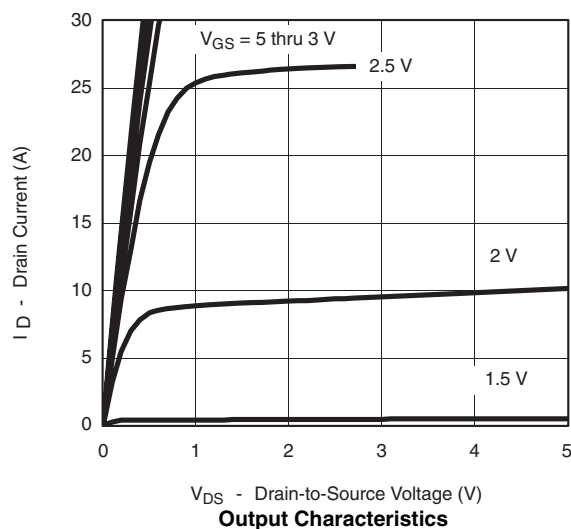
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

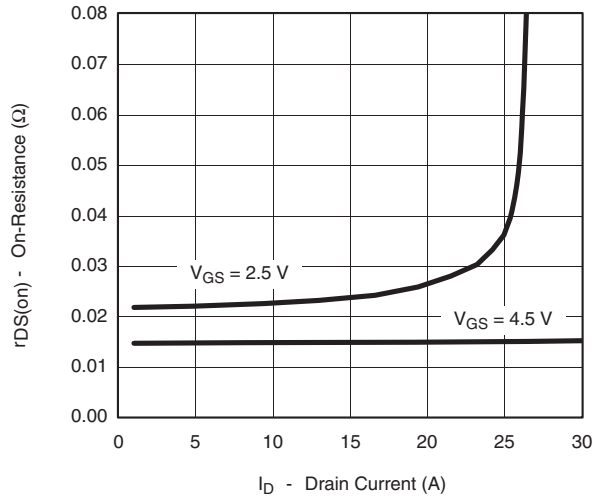
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

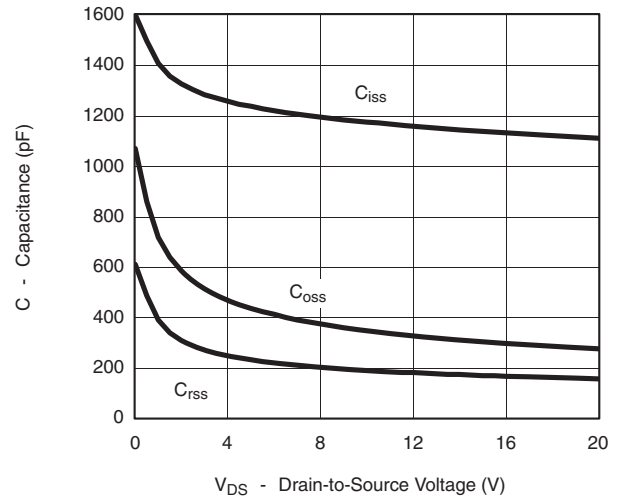
TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$ unless noted



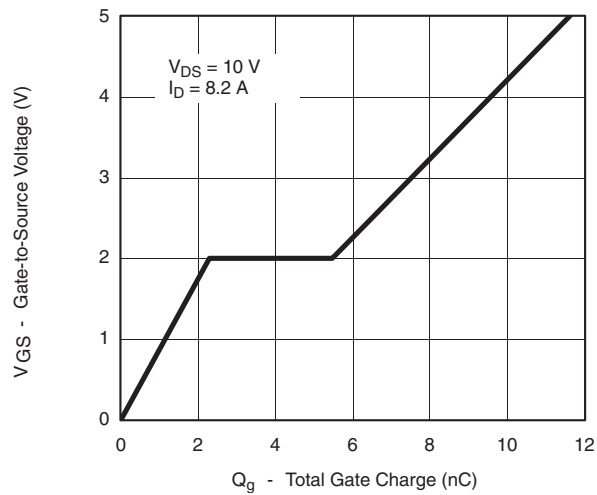
TYPICAL CHARACTERISTICS 25 °C unless noted



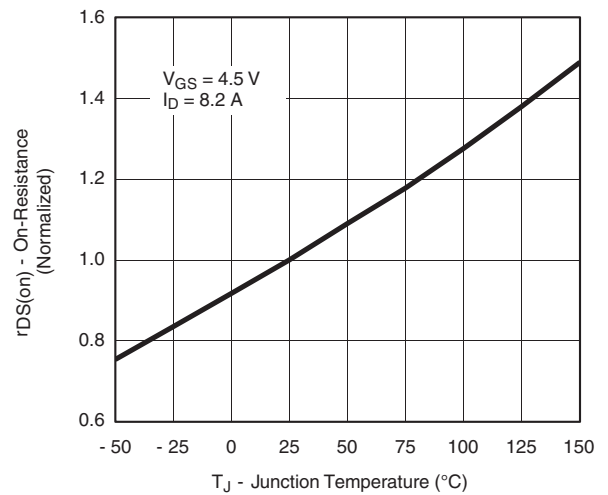
On-Resistance vs. Drain Current



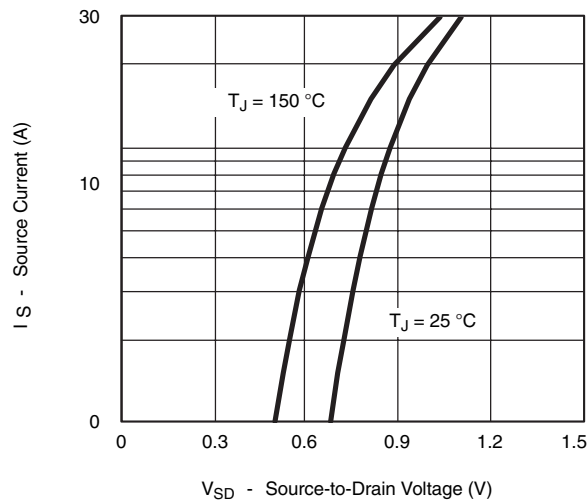
Capacitance



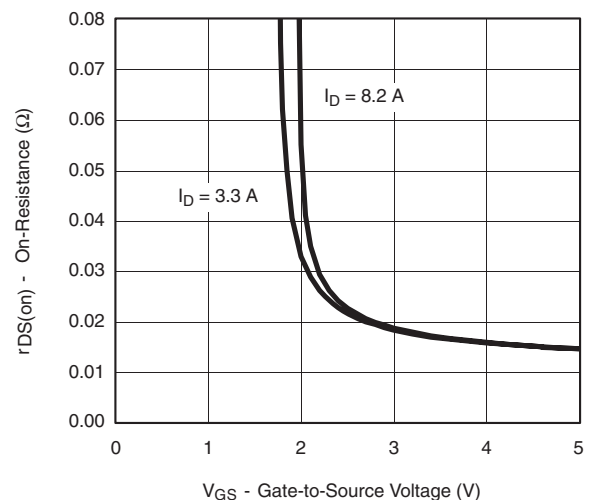
Gate Charge



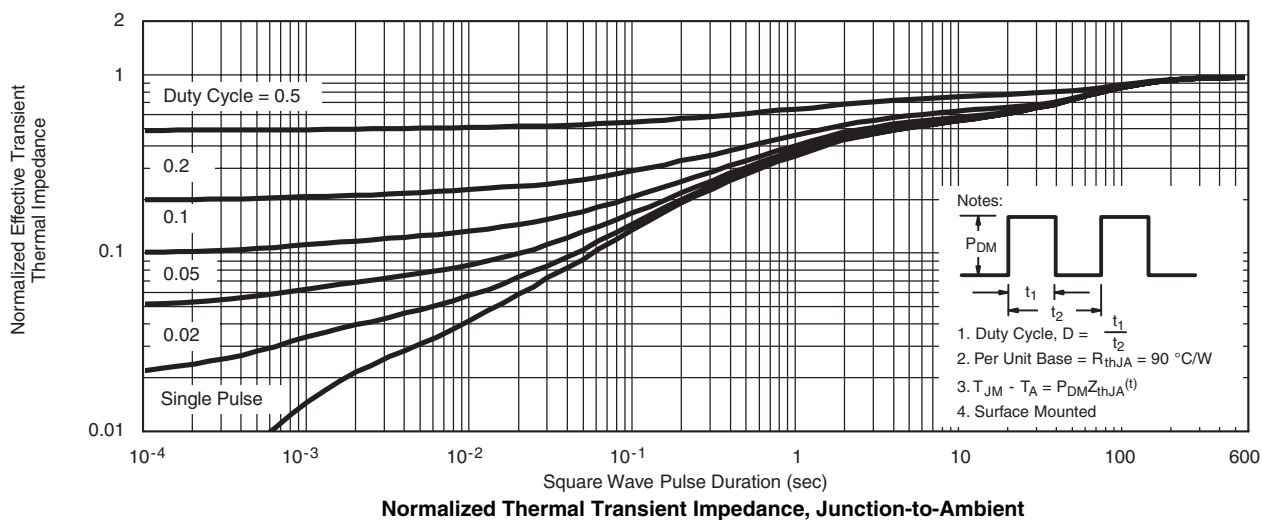
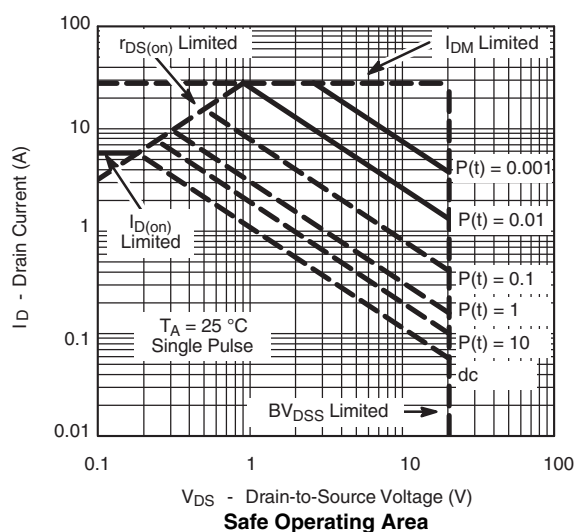
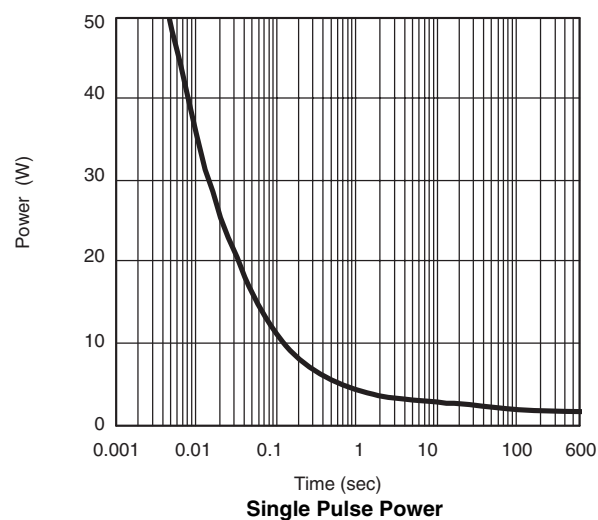
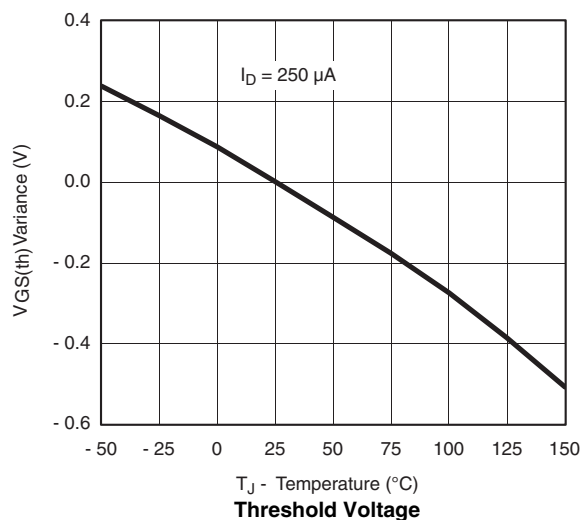
On-Resistance vs. Junction Temperature



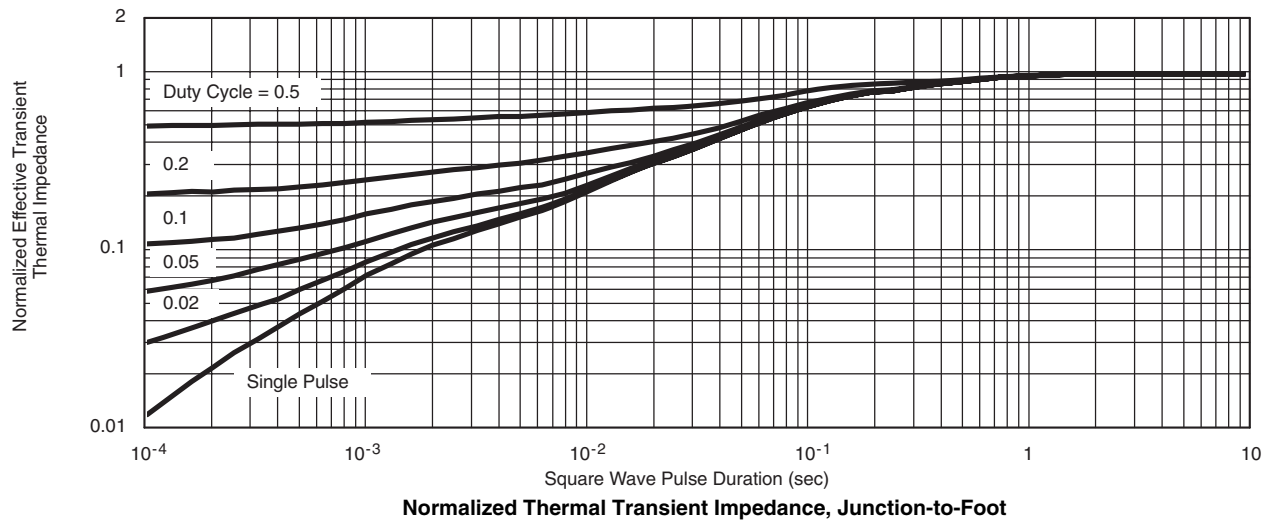
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

TYPICAL CHARACTERISTICS 25 °C unless noted

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